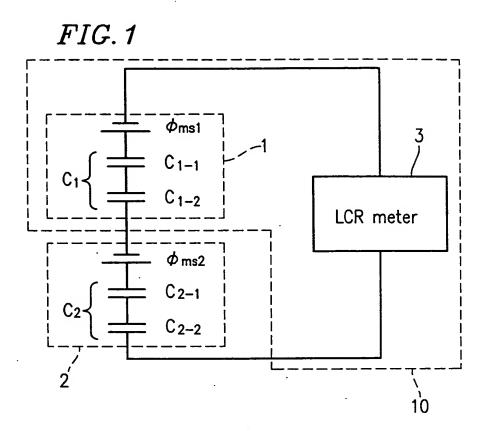
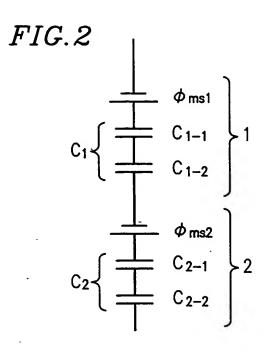
Inventor: OHMINAMI, Nobuyuki SN unknown/Sheet 1 of 9 Atty. Dkt.: 829-593

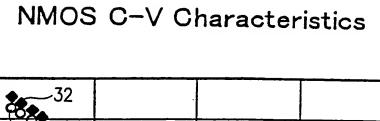


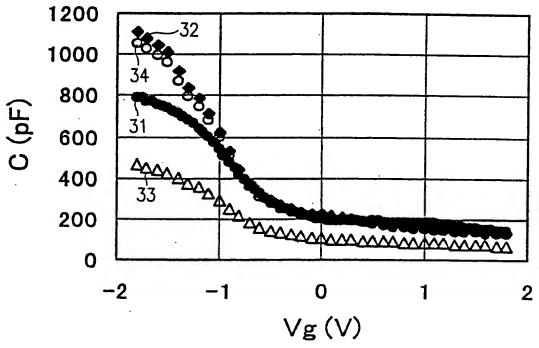
Inventor: OHMINAMI, Nobuyuki SN unknown/Sheet 2 of 9 Atty. Dkt.: 829-593



Inventor: OHMINAMI, Nobuyuki SN unknown/Sheet 3 of 9 Atty. Dkt.: 829-593

FIG.3





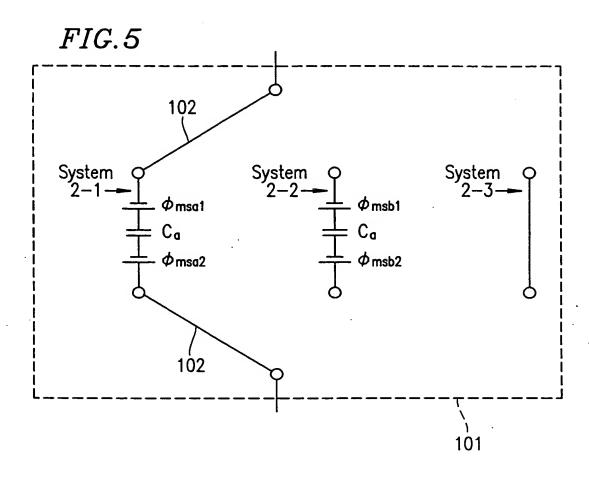
- 3.2nmC–V measured curve
- 2nmC-V ideal curve
- -△— Synthesis curve -O— 2nmC-V conversion curve

SN unknown/Sheet 4 of 9 Atty. Dkt.: 829-593

FIG. 4 **START** Serially connect MOS structure to be measured to capacitance structure having known capacitance S401 Measure synthesis capacitance S402 of serially-connected MOS structure and capacitance structure Calculate capacitance of MOS structure based on measured synthesis capacitance -S403

END

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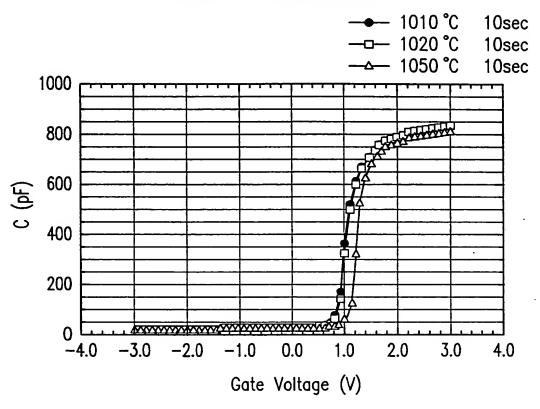


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PMOS C-V Characteristics



Active Area: 9E-4cm²

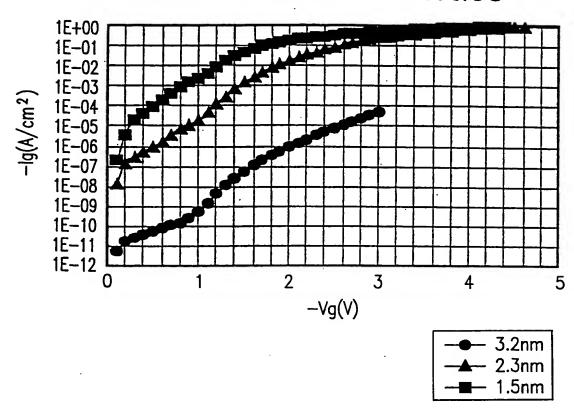
w/o Well Imp. Gate SiON: NO/N2

poly Si: 200nm P+lmp.: BF₂

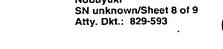
10003258.120601

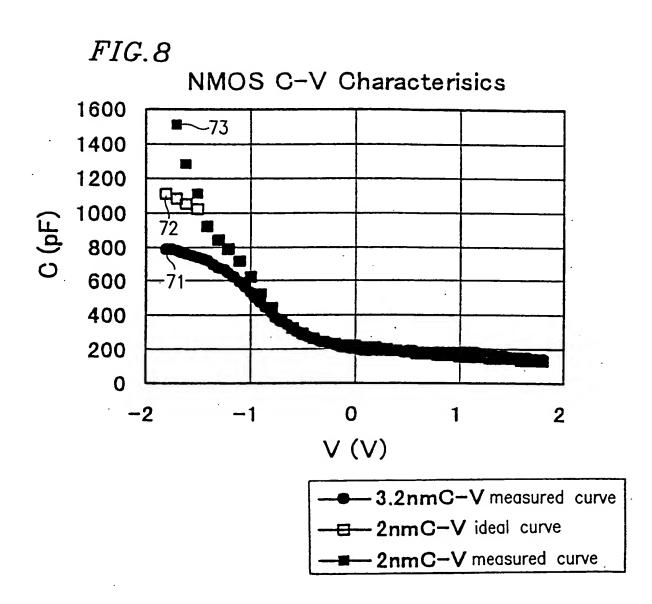
FIG. 7

NMOS I-V Characteristics



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